# 2SD2018

## Silicon NPN epitaxial planar type darlington

#### For low-frequency amplification

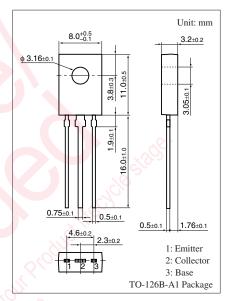
#### ■ Features

- High forward current transfer ratio hFE
- Built-in 60 V Zener diode between base to collector

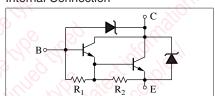
### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$60^{+25}_{-10}$	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$60^{+25}_{-10}$	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V	
Collector current	$I_{C}$	1	A	
Peak collector current	I <sub>CP</sub>	1.5	A	
Collector power $T_C = 25^{\circ}C$	$P_{C}$	1.2	W	
dissipation		5.0		
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	

Note) \*: With a  $100 \text{ mm} \times 100 \text{ mm} \times 2 \text{ mm}$  Al heat sick.



#### Internal Connection



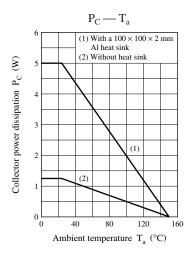
### ■ Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

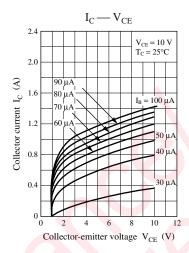
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 100 \mu\text{A},  I_E = 0$	50		85	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 1 \text{ mA}, I_B = 0$	50		85	V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}, I_{E} = 0$			1	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 4 \text{ V}, I_C = 0$			2	mA
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_{C} = 1.0 \text{ A}$	6500		40 000	_
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	$I_C = 1.0 \text{ A}, I_B = 1.0 \text{ mA}$			1.8	V
Base-emitter saturation voltage *	V <sub>BE(sat)</sub>	$I_C = 1.0 \text{ A}, I_B = 1.0 \text{ mA}$			2.2	V

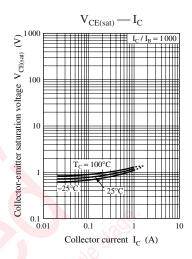
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

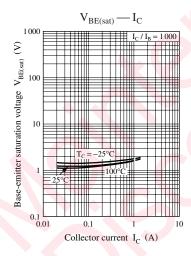
2. \*: Pulse measurement

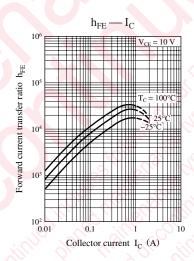
## **Panasonic**

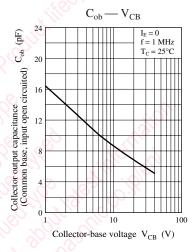












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